

DB# USPAT,US-PGPUB,EPO,JPO,DERWENT,IBM,DB#

Default operator: OR

(((((blocking adj layer) (etch adj stop))) with ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiO_n" "Si_n" "AlO_n"))); and dram) and capacitor) and ferroelectric and electrode with metallic

| | U | I | Document I | Issue Dat | Page | Title | Current O | Current X | Retrieval | Inventor | S | C | P | 2 | 3 | |
|---|---|---|-------------------|-----------|------|--------------------------|-----------|-----------|-----------|-----------------------|---|---|---|---|---|---|
| 1 | □ | □ | US 20030172003091 | 20 | | Ferroelectric memory dev | 438/3 | 257/295 | | Song, Yoon-Jong et al | □ | □ | □ | □ | □ | □ |
| 2 | □ | □ | US 20030052003032 | 79 | | Masking methods and et | 430/311 | 257/E21.0 | | Hwang, Jeng H. et al | □ | □ | □ | □ | □ | □ |
| 3 | □ | □ | US 62744242001081 | 14 | | Method for forming a ca | 438/239 | 257/E21.0 | | White, Jr., Bruce E. | □ | □ | □ | □ | □ | □ |
| 4 | □ | □ | US 61366592000102 | 8 | | Production process for a | 438/386 | 257/E21.0 | | Schindler, Gunther | □ | □ | □ | □ | □ | □ |
| 5 | □ | □ | US 61301022000101 | 13 | | Method for forming semi | 438/3 | 257/E21.0 | | White, Jr., Bruce E. | □ | □ | □ | □ | □ | □ |